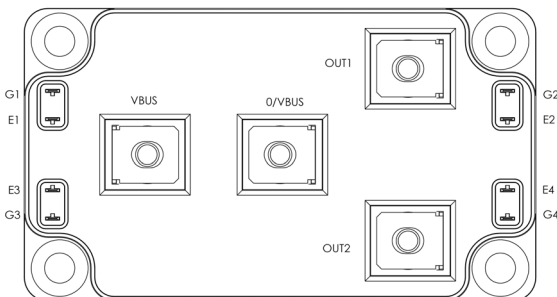
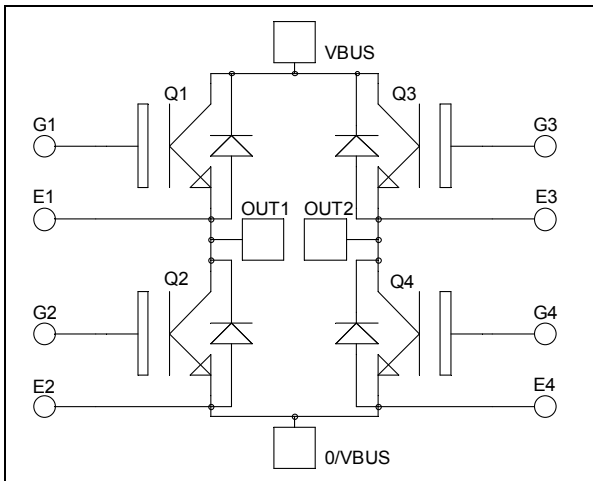


**Full bridge
High speed Trench + Field Stop IGBT4
Power module**

**$V_{CES} = 1200V$
 $I_C = 200A @ T_c = 80^{\circ}C$**


Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- High speed Trench + Field Stop IGBT 4 Technology
 - Low voltage drop
 - Low leakage current
 - Low switching losses
 - Soft recovery parallel diodes
 - Low diode VF
 - RBSOA and SCSOA rated
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

All ratings @ $T_j = 25^{\circ}C$ unless otherwise specified

Absolute maximum ratings (Per IGBT)

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Voltage	1200	V
I_C	Continuous Collector Current	$T_c = 25^{\circ}C$	350
		$T_c = 80^{\circ}C$	200
I_{CM}	Pulsed Collector Current	$T_c = 25^{\circ}C$	700
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_c = 25^{\circ}C$	1000
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	400A @ 1100V

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

Electrical Characteristics (Per IGBT)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$			100	μA
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15V$ $I_C = 200A$		2.05 2.6	2.4	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 7 mA$	5.2	5.8	6.4	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			340	nA

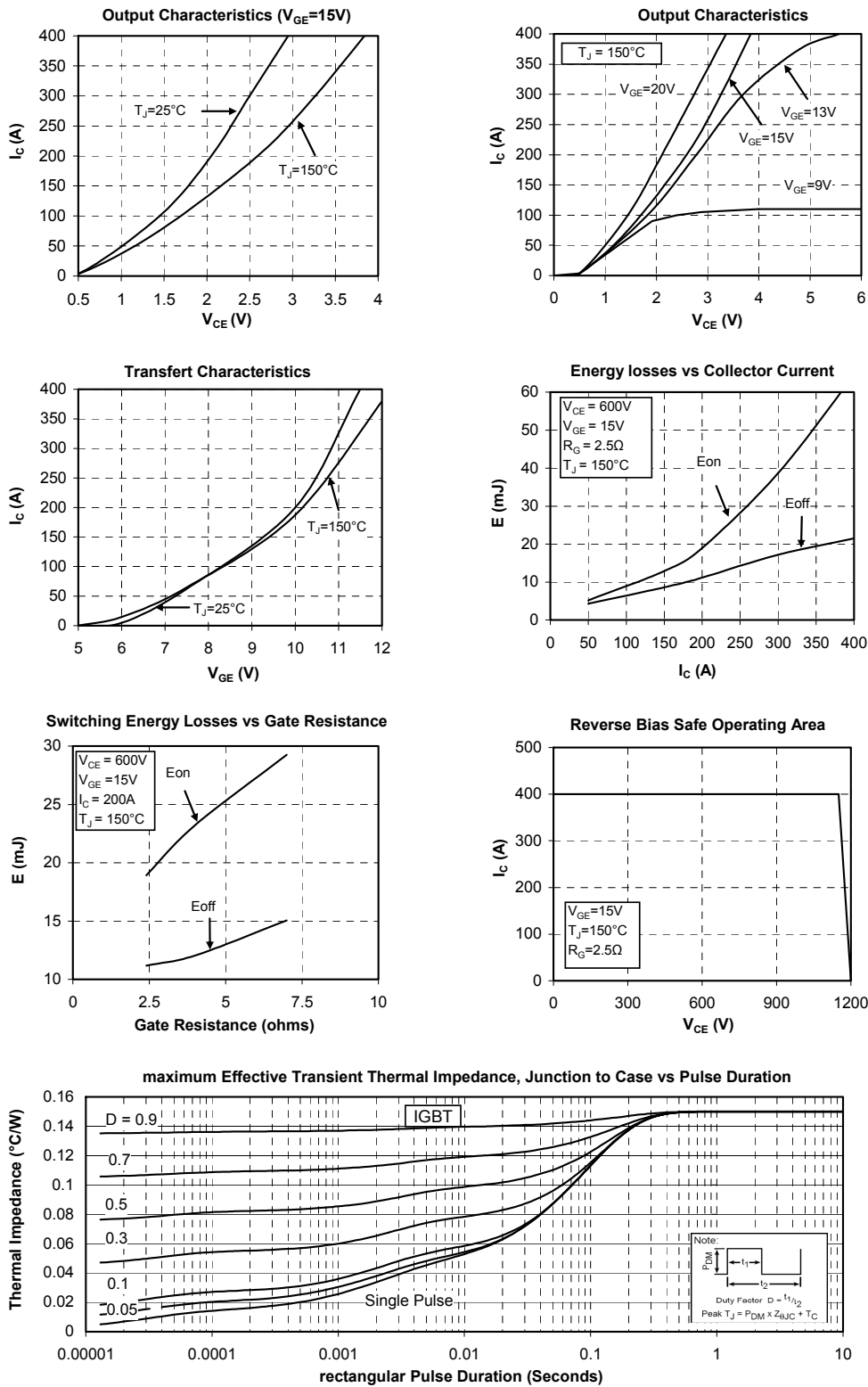
Dynamic Characteristics (Per IGBT)

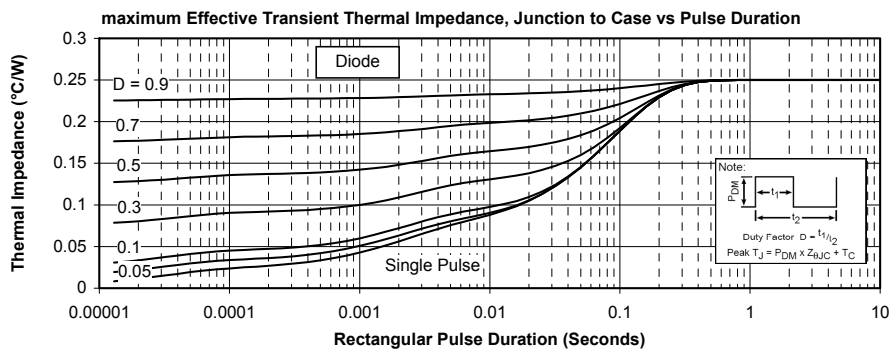
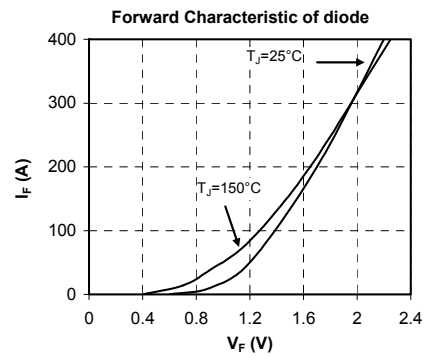
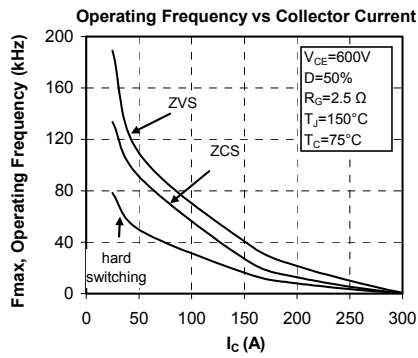
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V$		12.3		nF
C_{oes}	Output Capacitance	$V_{CE} = 25V$		0.7		
C_{res}	Reverse Transfer Capacitance	$f = 1MHz$		0.6		
Q_G	Gate charge	$V_{GE} = 15V ; V_{CE} = 960V$ $I_C = 200A$		900		nC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_C = 200A$ $R_G = 2.5\Omega$		30		ns
T_r	Rise Time			57		
$T_{d(off)}$	Turn-off Delay Time			290		
T_f	Fall Time			16		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_C = 200A$ $R_G = 2.5\Omega$		30		ns
T_r	Rise Time			49		
$T_{d(off)}$	Turn-off Delay Time			366		
T_f	Fall Time			48		
E_{on}	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_C = 200A$		18		mJ
E_{off}	Turn-off Switching Energy	$R_G = 2.5\Omega$		11		mJ
I_{sc}	Short Circuit data	$V_{GE} \leq 15V ; V_{Bus} = 600V$ $t_p \leq 10\mu s ; T_j = 150^\circ C$		700		A
R_{thJC}	Junction to Case Thermal Resistance				0.15	$^\circ C/W$

Diode ratings and characteristics (Per diode)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
V_{RRM}	Repetitive Reverse Voltage		1200			V	
I_{RM}	Reverse Leakage Current	$V_R = 1200V$			150	μA	
I_F	DC Forward Current	$T_C = 60^\circ C$		200		A	
V_F	Diode Forward Voltage	$I_F = 200A$ $V_{GE} = 0V$		1.9 1.85	2.2	V	
t_{rr}	Reverse Recovery Time	$I_F = 200A$ $V_R = 600V$ $di/dt = 4000A/\mu s$		155 300		ns	
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ C$ $T_j = 150^\circ C$		18.6 39		
E_r	Reverse Recovery Energy		$T_j = 25^\circ C$ $T_j = 150^\circ C$		8 16		mJ
R_{thJC}	Junction to Case Thermal Resistance					0.25	

Typical Performance Curve





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